

74LV132-Q100

Quad 2-input NAND Schmitt trigger

Rev. 1 — 11 November 2013

Product data sheet

1. General description

The 74LV132-Q100 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC132-Q100 and 74HCT132-Q100.

The 74LV132-Q100 contains four 2-input NAND gates which accept standard input signals. These gates are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The gate switches at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7\text{ V}$ and $V_{CC} = 3.6\text{ V}$
- Typical output ground bounce $< 0.8\text{ V}$ at $V_{CC} = 3.3\text{ V}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$
- Typical HIGH-level output voltage (V_{OH}) undershoot: $> 2\text{ V}$ at $V_{CC} = 3.3\text{ V}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Multiple package options

3. Applications

- Wave and pulse shapers for highly noisy environments
- Astable multivibrators
- Monostable multivibrators

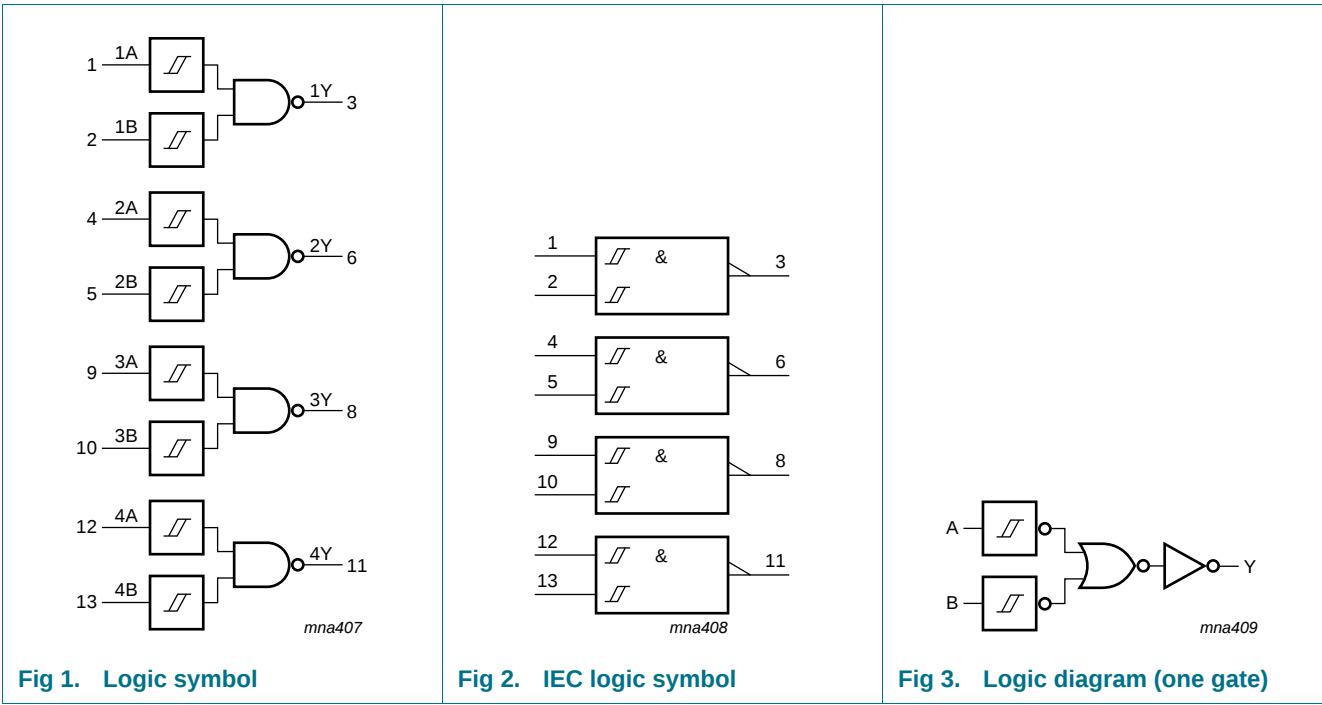


4. Ordering information

Table 1. Ordering information

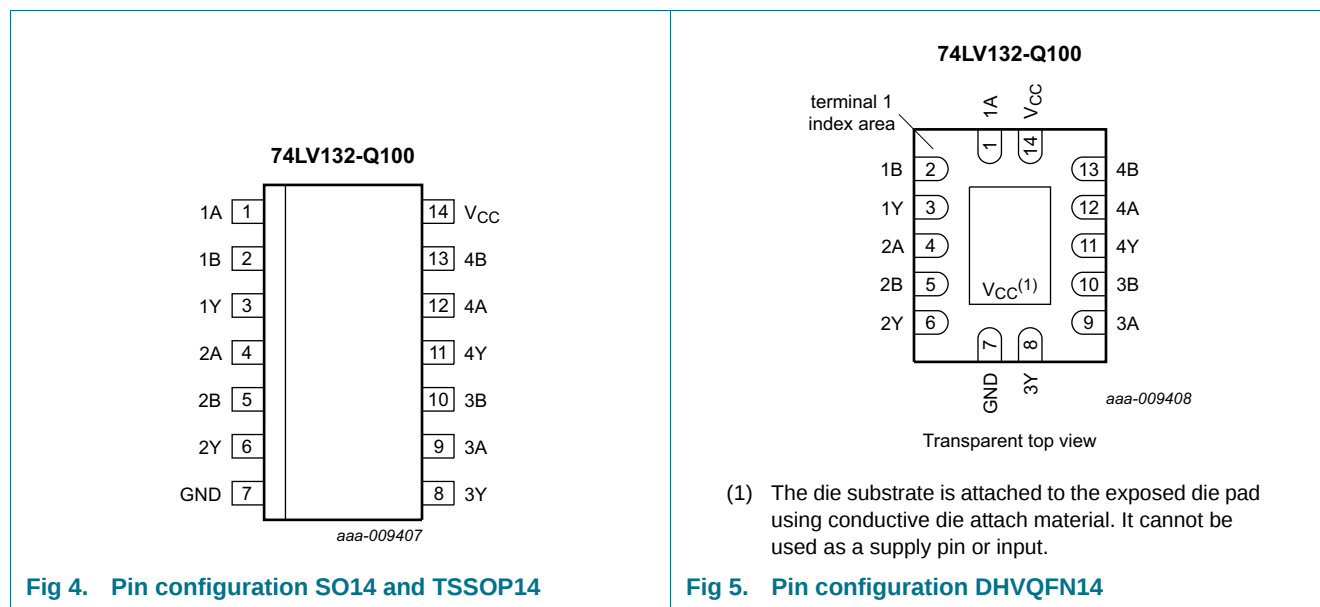
Type number	Package			
	Temperature range	Name	Description	Version
74LV132D-Q100	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV132PW-Q100	−40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV132BQ-Q100	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V _{CC}	14	supply voltage

7. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	± 50	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$			
	SO14 package		[2] -	500	mW
	TSSOP14 package		[3] -	500	mW
	DHVQFN14 package		[4] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

[3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage	[1]	1.0	3.3	5.5	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C

[1] The static characteristics are guaranteed from V_{CC} = 1.2 V to V_{CC} = 5.5 V. LV devices are guaranteed to function down to V_{CC} = 1.0 V (with input levels GND or V_{CC}).

10. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-}						
		I _O = -100 µA; V _{CC} = 1.2 V	-	1.2	-	-	-	V
		I _O = -100 µA; V _{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I _O = -100 µA; V _{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I _O = -100 µA; V _{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		I _O = -100 µA; V _{CC} = 4.5 V	4.3	4.5	-	4.3	-	V
		I _O = -6 mA; V _{CC} = 3.0 V	2.4	2.82	-	2.2	-	V
		I _O = -12 mA; V _{CC} = 4.5 V	3.6	4.2	-	3.5	-	V
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T-}						
		I _O = 100 µA; V _{CC} = 1.2 V	-	0	-	-	-	V
		I _O = 100 µA; V _{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	-	1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	20.0	-	40	µA
ΔI _{CC}	additional supply current	per input; V _I = V _{CC} - 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	µA
C _I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 7. Dynamic characteristics

$GND = 0\text{ V}$; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay	nA, nB to nY; see Figure 6 ^[2]						
		$V_{CC} = 1.2\text{ V}$	-	65	-	-	-	ns
		$V_{CC} = 2.0\text{ V}$	-	18	34	-	43	ns
		$V_{CC} = 2.7\text{ V}$	-	15	24	-	30	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$; $C_L = 15\text{ pF}$ ^[3]	-	10	-	-	-	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ ^[3]	-	12	20	-	25	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$ ^[3]	-	9.0	14	-	17	ns
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}$; $f_i = 1\text{ MHz}$; $V_i = GND\text{ to }V_{CC}$ ^[4]	-	24	-	-	-	pF

[1] All typical values are measured at $T_{amb} = 25\text{ °C}$.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3\text{ V}$ and $V_{CC} = 5.0\text{ V}$).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz, f_o = output frequency in MHz

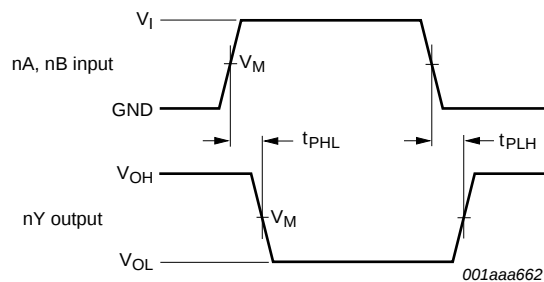
C_L = output load capacitance in pF

V_{CC} = supply voltage in V

N = number of inputs switching

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



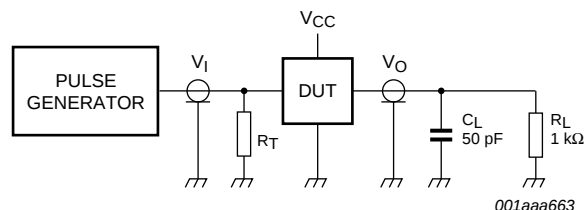
Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA, nB) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage V_{CC}	Input V_M	Output V_M
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

Fig 7. Load circuit for switching times

Table 9. Test data

Supply voltage V_{CC}	Input V_I	t_r, t_f
< 2.7 V	V_{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	V_{CC}	≤ 2.5 ns

13. Transfer characteristics

Table 10. Transfer characteristics

$GND = 0$ V; for test circuit, see [Figure 7](#).

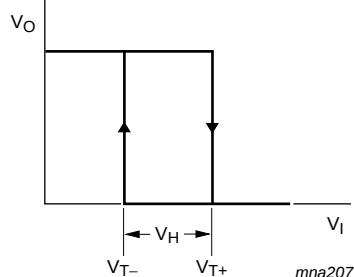
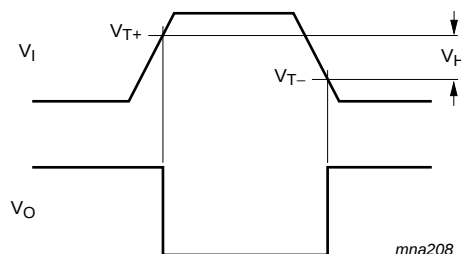
Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V_{T+}	positive-going threshold voltage	see Figure 6						
		$V_{CC} = 1.2$ V	-	0.70	-	-	-	V
		$V_{CC} = 2.0$ V	0.8	1.10	1.4	0.8	1.4	V
		$V_{CC} = 2.7$ V	1.0	1.45	2.0	1.0	2.0	V
		$V_{CC} = 3.0$ V	1.2	1.60	2.2	1.2	2.2	V
		$V_{CC} = 3.6$ V	1.5	1.95	2.4	1.5	2.4	V
		$V_{CC} = 4.5$ V	1.7	2.50	3.2	1.7	3.2	V
		$V_{CC} = 5.5$ V	2.1	3.00	3.9	2.1	3.9	V

Table 10. Transfer characteristics ...continuedGND = 0 V; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V_{T-}	negative-going threshold voltage	see Figure 6						
		$V_{CC} = 1.2$ V	-	0.34	-	-	-	V
		$V_{CC} = 2.0$ V	0.3	0.65	0.9	0.3	0.9	V
		$V_{CC} = 2.7$ V	0.4	0.90	1.4	0.4	1.4	V
		$V_{CC} = 3.0$ V	0.6	1.05	1.5	0.6	1.5	V
		$V_{CC} = 3.6$ V	0.8	1.30	1.8	0.8	1.8	V
		$V_{CC} = 4.5$ V	0.9	1.60	2.0	0.9	2.0	V
		$V_{CC} = 5.5$ V	1.2	2.00	2.6	1.2	2.6	V
V_H	hysteresis voltage ($V_{T+} - V_{T-}$); see Figure 6							
		$V_{CC} = 1.2$ V	-	0.3	-	-	-	V
		$V_{CC} = 2.0$ V	0.2	0.55	0.8	0.2	0.8	V
		$V_{CC} = 2.7$ V	0.3	0.60	1.1	0.3	1.1	V
		$V_{CC} = 3.0$ V	0.4	0.65	1.2	0.4	1.2	V
		$V_{CC} = 3.6$ V	0.4	0.70	1.2	0.4	1.2	V
		$V_{CC} = 4.5$ V	0.4	0.80	1.4	0.4	1.4	V
		$V_{CC} = 5.5$ V	0.6	1.00	1.5	0.6	1.5	V

[1] All typical values are measured at $T_{amb} = 25$ °C.

14. Waveforms transfer characteristics

**Fig 8. Transfer characteristic** V_{T+} and V_{T-} limits at 70 % and 20 %.**Fig 9. Definition of V_{T+} , V_{T-} and V_H**

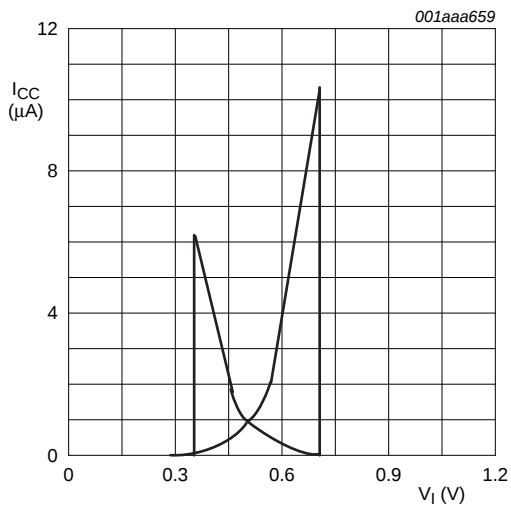


Fig 10. Typical 74LV132-Q100 transfer characteristics

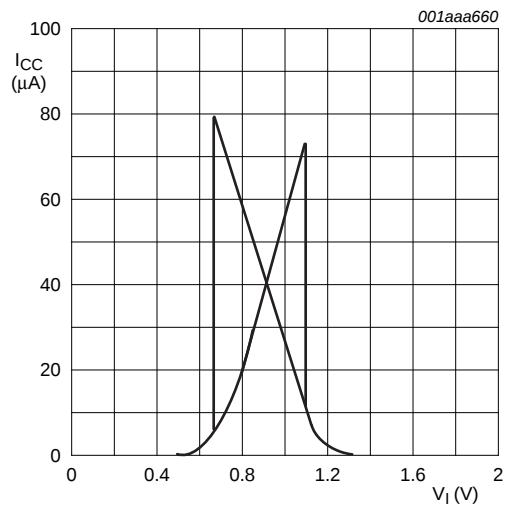


Fig 11. Typical 74LV132-Q100 transfer characteristics

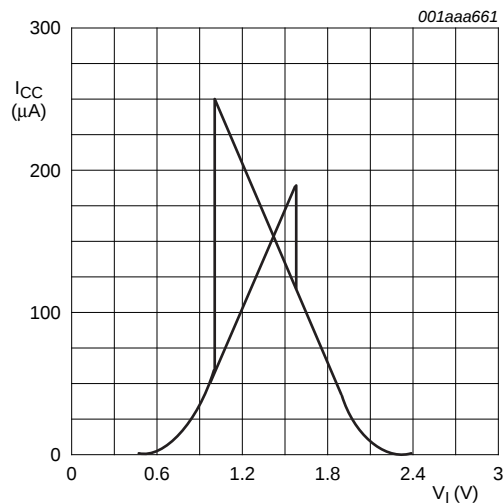


Fig 12. Typical 74LV132-Q100 transfer characteristics

15. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

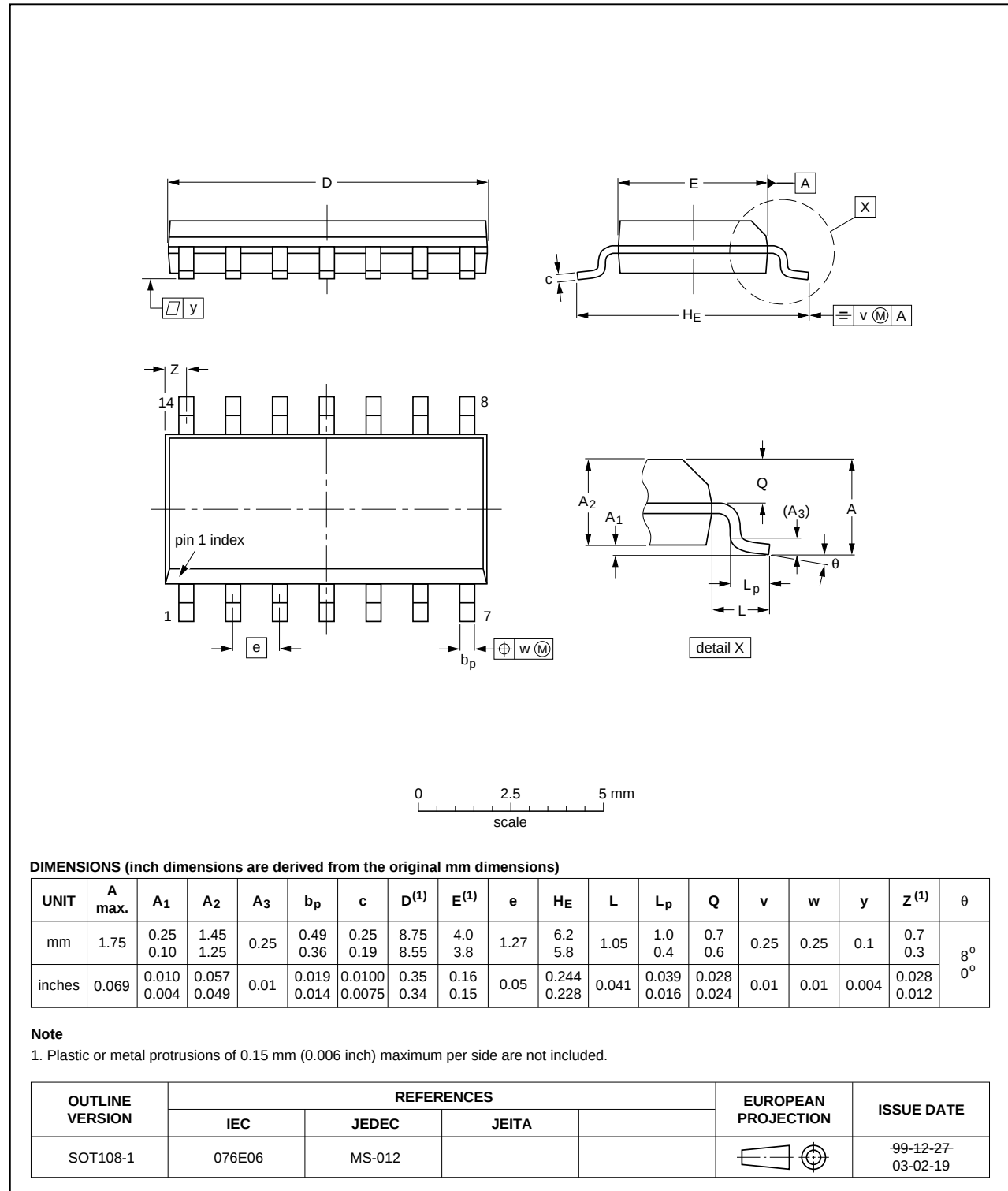


Fig 13. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

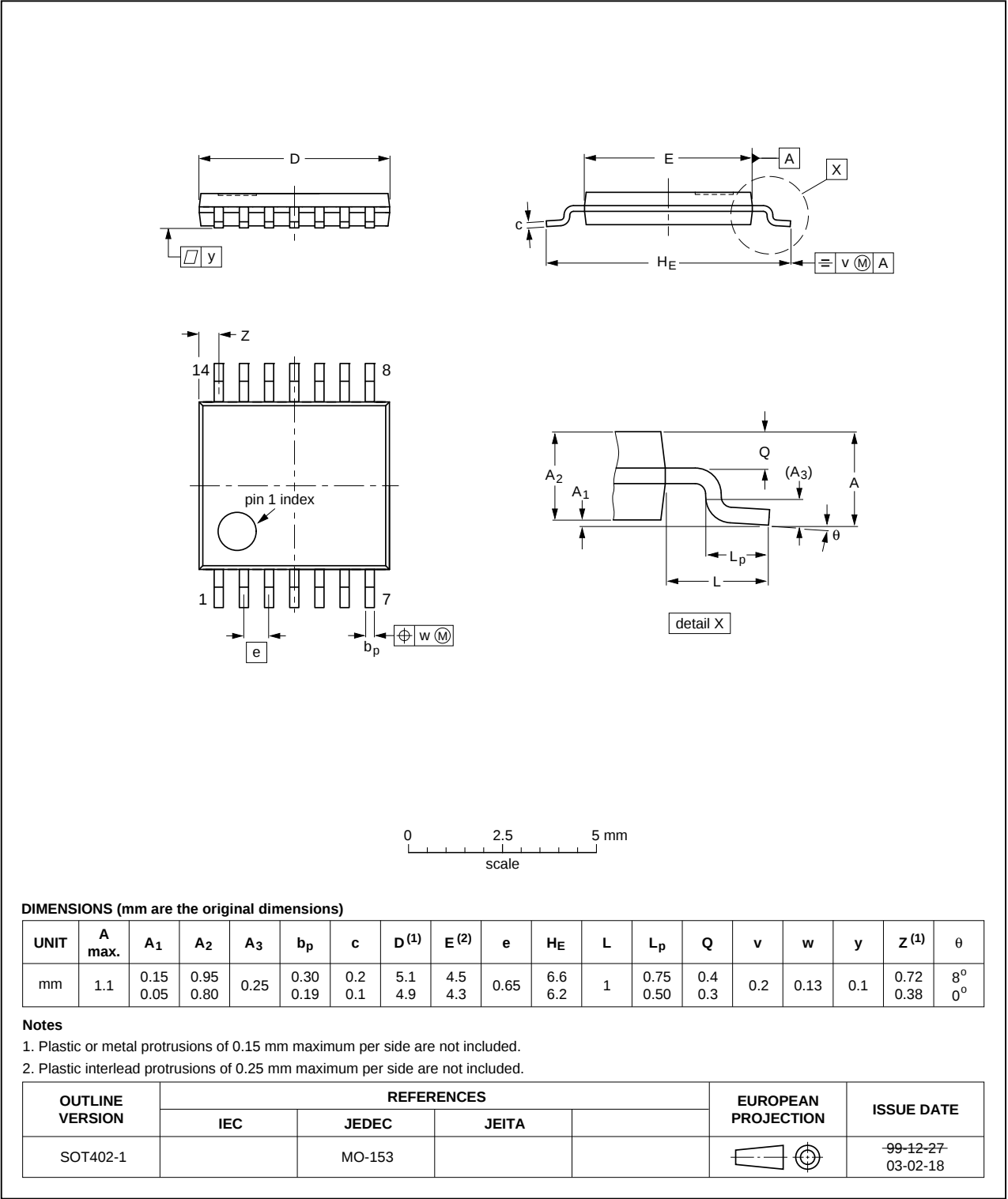


Fig 14. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

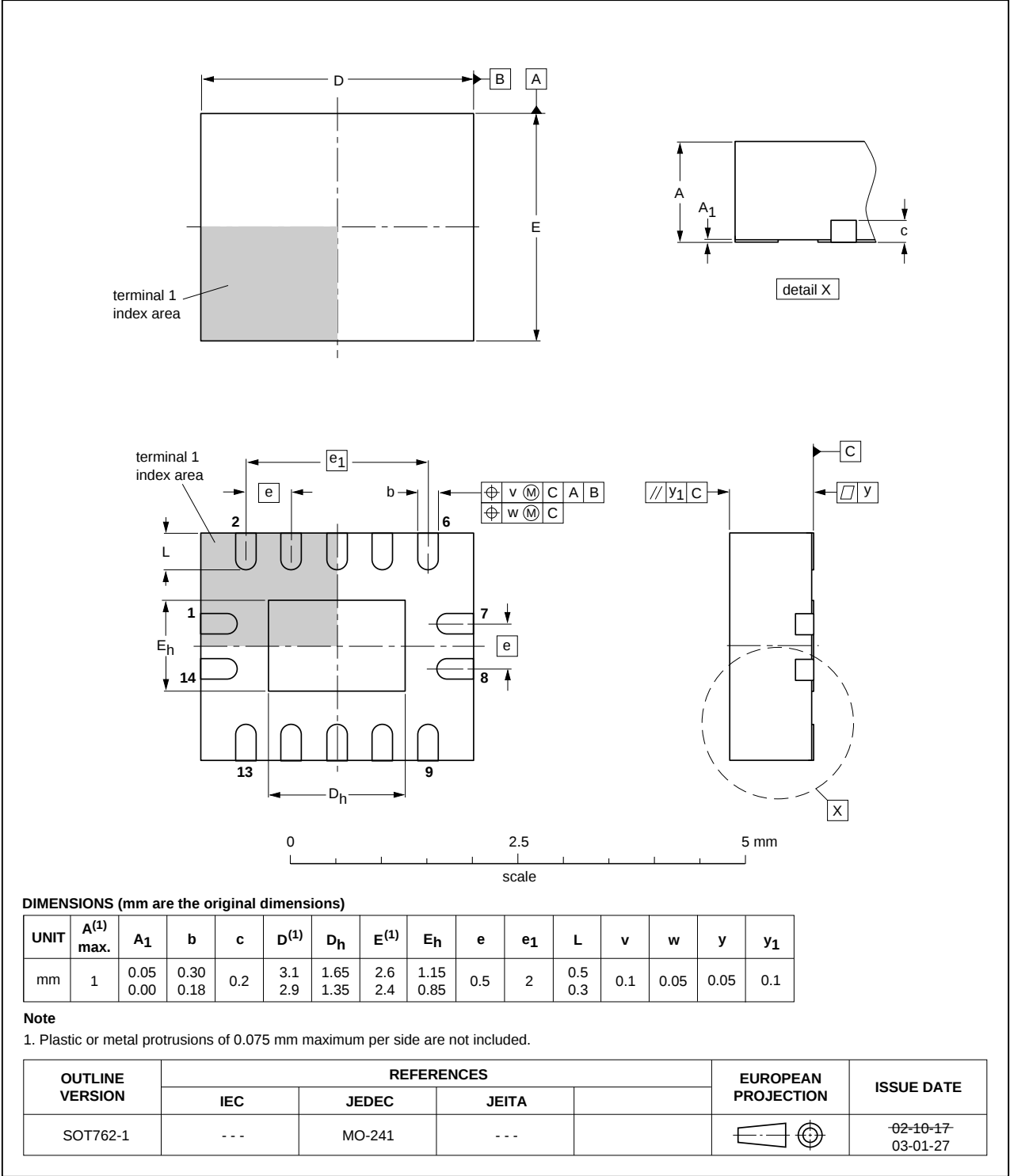


Fig 15. Package outline SOT762-1 (DHVQFN14)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV132_Q100 v.1	20131111	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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